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December 2013

FDPF10N60ZUT

N-Channel UniFETTM Ultra FRFETTM MOSFET 600 V, 9 A, 800 m Ω

Features

- $R_{DS(on)}$ = 650 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 31 nC)
- Low C_{rss} (Typ. 15 pF)
- 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

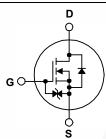
Applications

- LCD/LED/PDP TV
- · Lighting
- · Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. UniFET II Ultra FRFETTM MOSFET has much superior body diode reverse recovery performance. Its $t_{\rm rr}$ is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET II Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDPF10N60ZUT	Unit
V _{DSS}	Drain to Source Voltage			600	V
V _{GSS}	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T _C = 25°C)		9*	А
ID	Dialii Guirent	- Continuous (T _C = 100°C)		5.4*	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	36*	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	100	mJ
I _{AR}	Avalanche Current		(Note 1)	9	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/d	It	(Note 3)	20	V/ns
D	Dower Dissinction	(T _C = 25°C)		42	W
P_{D}	Power Dissipation	- Derate Above 25°C		0.3	W/°C
T _J , T _{STG}	Operating and Storage Ter	mperature Range		-55 to +150	οС
T _L	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5	Seconds	300	°C

^{*}Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter FDPF10N60ZUT		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	-0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF10N60ZUT	FDPF10N60ZUT	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	600	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.8	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	25	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	250	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±10	μΑ

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$	-	0.65	0.80	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 4.5 A	-	12.5	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	1490	1980	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	-	230	240	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	-\	15	25	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 10 A,	- \	31	40	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	- \	8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	12	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	25	60	ns
t _r		$V_{DD} = 300 \text{ V}, I_D = 10 \text{ A},$	-	40	90	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25 \Omega$, $V_{GS} = 10 V$	-	95	200	ns
t _f	Turn-Off Fall Time	(Note	-	60	130	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	9*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	36	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 10 A	-	-	1.6	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 10 A,	-	45	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	52	/ -	nC

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 2 mH, I $_{AS}$ = 10 A, V $_{DD}$ = 50 V, R_{G} = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$
- 3. $I_{SD} \le 10$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}C$.
- Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

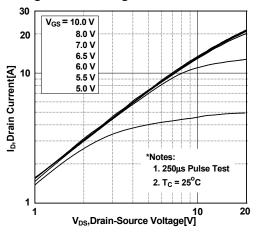


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

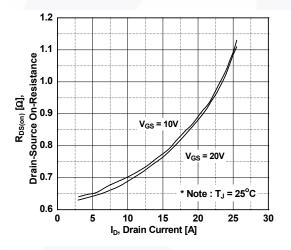


Figure 5. Capacitance Characteristics

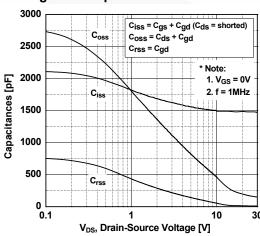


Figure 2. Transfer Characteristics

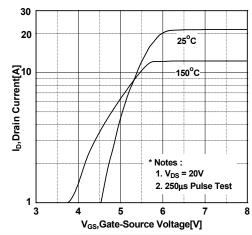


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

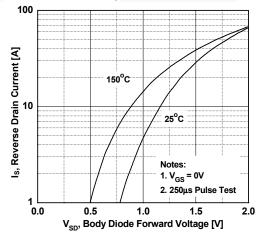
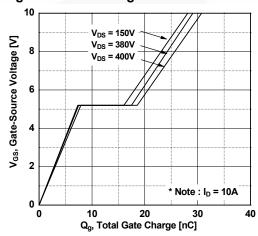


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperaure

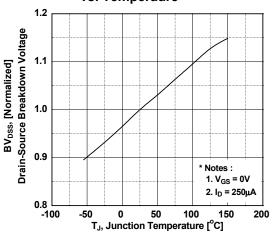


Figure 8. Maximum Safe Operating Area

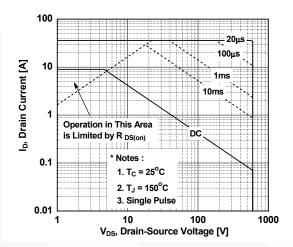


Figure 9. Maximum Drain Current vs. Case Temperature

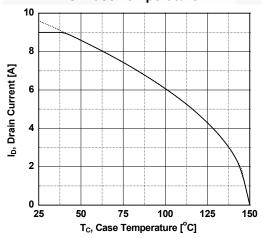
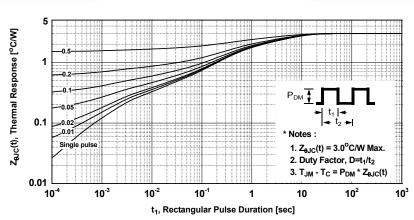


Figure 10. Transient Thermal Response Curve



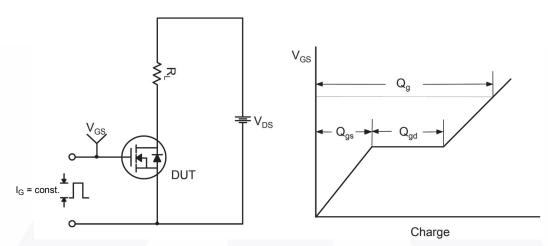


Figure 11. Gate Charge Test Circuit & Waveform

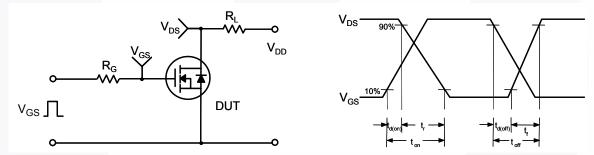


Figure 12. Resistive Switching Test Circuit & Waveforms

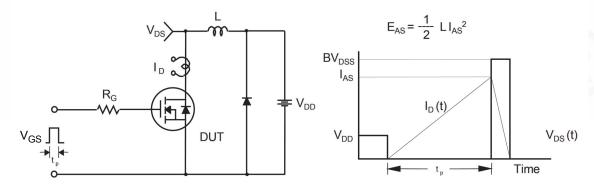


Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms

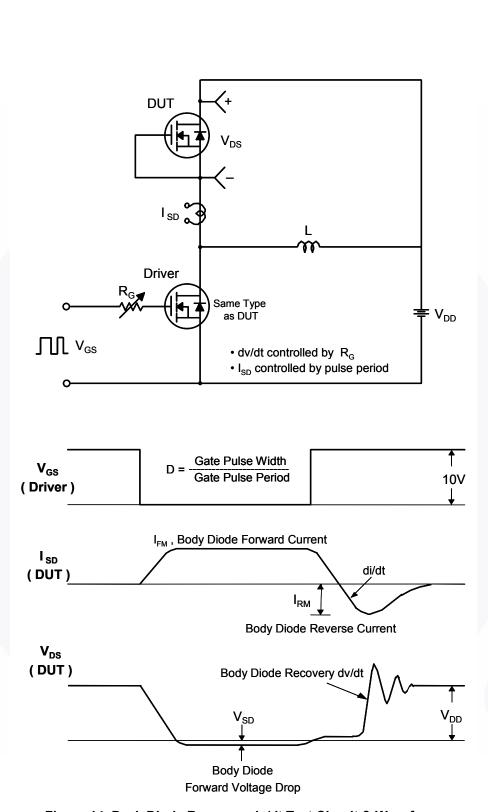


Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

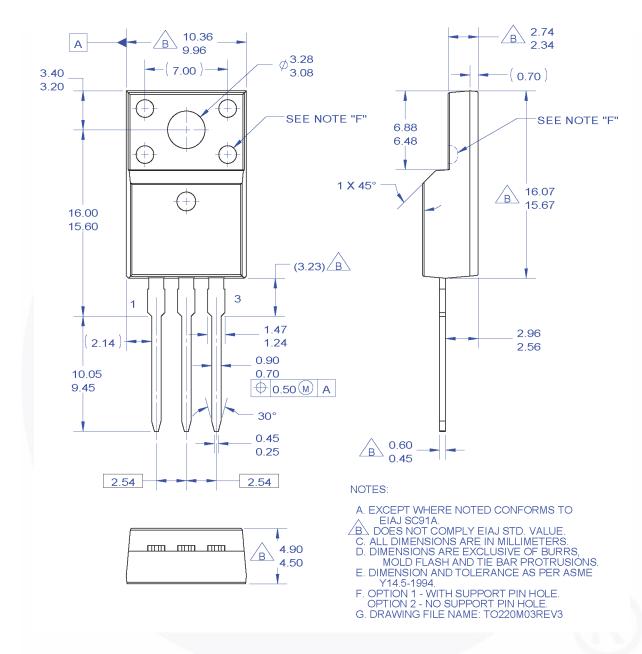


Figure 15. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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